OPB732, OPB732WZ



Features:

- PC board mounting (OPB732)
- 24" (610 mm) 26 AWG wired with mounting tabs (OPB732WZ)
- Non-contact infrared switch
- Up to 1" or more reflective distance depending on circuitry



Description:

OPB732 uses an Infrared LED and Phototransistor in a reflective switch configuration. The assembly is offered with either PCBoard through hole pins (**OPB732**) or 24" (610 mm), 26 AWG wires (**OPB732WZ**), and uses an opaque housing to reduce the sensor's ambient light sensitivity. The emitter and sensor are protected by a clear window, providing a device that can operate in a dusty environment. The phototransistor can be configured as a Common Collector or Common Emitter device.

While an object is in the reflective path of the device, light from the LED will be reflected back to the housing irradiating the surface (base) of the phototransistor. When Infrared light strikes the phototransistor, the transistor becomes forward biased and is considered to be in the "ON" state, providing an $I_{C(ON)}$ current proportional to the light striking the phototransistor. With the Infrared light from the LED not being reflected to the phototransistor, the phototransistor turns "OFF," minimizing the $I_{C(ON)}$ current.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

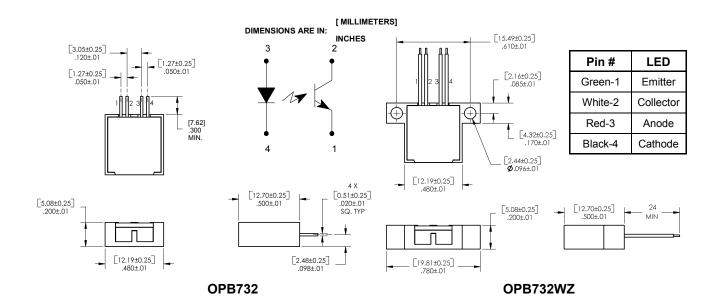
- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Equipment security
- Door sensor
- Machine safety
- End of travel sensor

	Ordering Info	ormation		
Part Number	LED Peak Wavelength	Lead Length / Spacing		
OPB732	850 nm	0.150"/ see diagram		
OPB732WZ	000 11111	24" / 26 AWG Wire		



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Electrical Specifications

Absolute	Maximum Ratings (T _A = 25° C unless of	otherw	ise not	ed)			
Storage 7	Temperature						-40° C to +100° C
Operatin	g Temperature						-40° C to +85° C
Lead Solo	dering Temperature (1/16" (1.6mm) from ca	se for 5	secono	ds with s	soldering i	ron) ⁽²⁾	260° C
LED							
Forward	Current						50 mA
Peak For	ward current (2 μs pulse width, 0.1% Duty C	Cycle)					1 A
Reverse	DC Voltage						3 V
Power Di	ssipation						100 mW
Output Ph	oto Transistor						
Collector	-Emitter Voltage						30 V
Collector	DC Current						50 mA
Power Di	ssipation						100 mW
Electrical	Characteristics (T _A = 25° C unless other	wise no	ted)				
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TES	T CONDITIONS
Input LED	(See OP265 for additional information, re	ference	only)				
V_{F}	Forward Voltage	-	-	1.8	V	I _F = 20 mA	
		i e	i e				

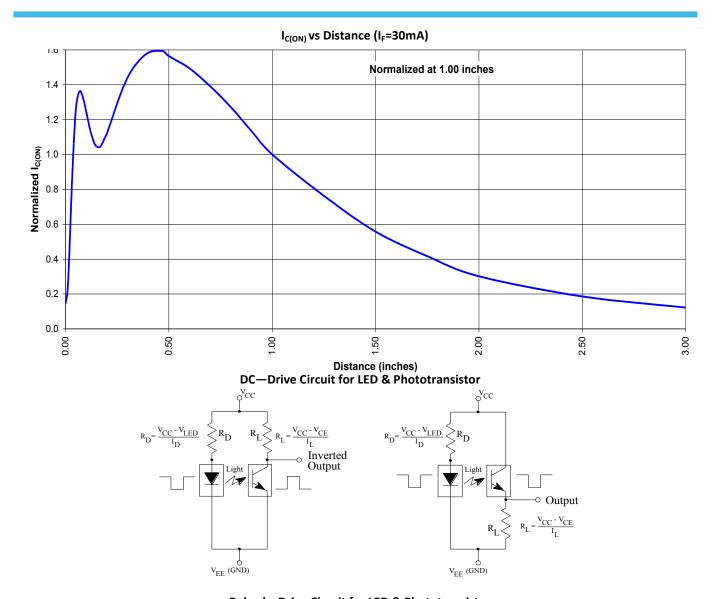
Electrical	Characteristics ($T_A = 25^{\circ}$ C unless otherw	wise no	ted)				
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input LED	(See OP265 for additional information, re	ference	only)				
V_{F}	Forward Voltage	-	-	1.8	٧	I _F = 20 mA	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V	
Output Ph	ototransistor (See OP505 for additional ir	nforma	tion, ref	erence	only)		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	٧	$I_C = 100 \mu\text{A}, E_E = 0 \text{mw/cm}^2$	
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	$V_{CE} = 10 \text{ V, } E_E = 0 \text{ mw/cm}^2$	
Coupled							
V _{CE(SAT)}	Collector-Emitter Saturation Voltage ⁽⁴⁾	-	-	0.4	V	$I_C = 250 \mu\text{A}, I_F = 30 \text{mA}$, (4)	
I _{C(ON)}	On-State Collector Current ⁽⁴⁾	0.25	-	-	mA	$V_{CE} = 1 V, I_F = 30 mA, (4)$	
I _{cx}	Cross Talk	-	-	50	μΑ	V_{CE} = 5 V, I_F = 30 mA, No reflective surface	

Notes:

- (1) All parameters tested using pulse technique.
- (2) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.
- (4) Distance = 1" (from front of package to a 90% diffuse reflective white card)

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Pulsed—Drive Circuit for LED & Phototransistor

